MOSFET – Small Signal, Complementary, SC-88

20 V / -8.0 V, +0.63 A / -0.775 A

NTJD4105C

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D Max
N−Ch 20 V	0.29 Ω @ 4.5 V	0.63 A
	0.36 Ω @ 2.5 V	
P−Ch −8.0 V	0.22 Ω @ −4.5 V	−0.775 A
	0.32 Ω @ −2.5 V	
	0.51 Ω @ −1.8 V	

Features

- Complementary N and P Channel Device
- Leading −8.0 V Trench for Low $R_{DS(on)}$ Performance
- ESD Protected Gate − ESD Rating: Class 1
- SC−88 Package for Small Footprint (2 x 2 mm)
- Pb−Free Packages are Available

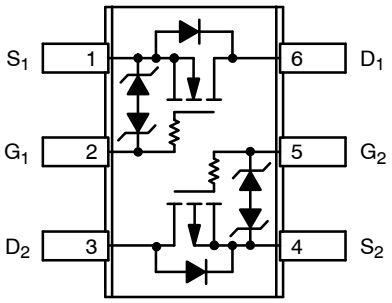
Applications

- DC−DC Conversion
- Load/Power Switching
- Single or Dual Cell Li−Ion Battery Supplied Devices
- Cell Phones, MP3s, Digital Cameras, PDAs



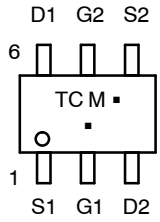
SC−88/SOT−363
CASE 419B
STYLE 28

SOT−363
SC−88 (6−LEADS)



Top View

MARKING DIAGRAM & PIN ASSIGNMENT



TC = Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Symbol	Parameter			Value	Unit
V_{DSS}	Drain−to−Source Voltage		N−Ch	20	V
			P−Ch	−8.0	
V_{GS}	Gate−to−Source Voltage		N−Ch	±12	V
			P−Ch	±8.0	
I_D	Continuous Drain Current − Steady State (Based on $R_{\theta JA}$)	N−Ch	T_A = 25°C	0.63	A
			T_A = 85°C	0.46	
		P−Ch	T_A = 25°C	−0.775	
			T_A = 85°C	−0.558	
	Continuous Drain Current − Steady State (Based on $R_{\theta JL}$)	N−Ch	T_A = 25°C	0.91	
			T_A = 85°C	0.65	
		P−Ch	T_A = 25°C	−1.1	
			T_A = 85°C	−0.8	
I_{DM}	Pulsed Drain Current		tp ≤ 10 μs	±1.2	A
P_D	Power Dissipation − Steady State (Based on $R_{\theta JA}$)		T_A = 25°C	0.27	W
			T_A = 85°C	0.14	
	Power Dissipation − Steady State (Based on $R_{\theta JL}$)		T_A = 25°C	0.55	
			T_A = 85°C	0.29	
T_J, T_{STG}	Operating Junction and Storage Temperature			−55 to 150	°C
I_S	Source Current (Body Diode)		N−Ch	0.63	A
			P−Ch	−0.775	
T_L	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS (Note 1).

Symbol	Parameter		Value	Unit
$R_{\theta JA}$	Junction−to−Ambient − Steady State	Typ	400	°C/W
		Max	460	
$R_{\theta JL}$	Junction−to−Lead (Drain) − Steady State	Typ	194	
		Max	226	

1. Surface mounted on FR4 board using 1 oz Cu area = 0.9523 in sq.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 7.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	N/P	Test Condition		Min	Typ	Max	Units
OFF CHARACTERISTICS								
$V_{(BR)DSS}$	Drain−to−Source Breakdown Voltage	N	V_{GS} = 0 V	I_D = 250 μA	20	27		V
		P		I_D = −250 μA	−8.0	−10.5		
$V_{(BR)DSS}$ / T_J	Drain−to−Source Breakdown Voltage Temperature Coefficient	N				22		mV/ °C
		P				−6.0		
I_{DSS}	Zero Gate Voltage Drain Current	N	V_{GS} = 0 V, V_{DS} = 16 V	T_J = 25 °C			1.0	μA
		P	V_{GS} = 0 V, V_{DS} = −6.4 V				1.0	
I_{GSS}	Gate−to−Source Leakage Current	N	V_{DS} = 0 V	V_{GS} = ±12 V			10	μA
		P		V_{GS} = ±8.0			10	
ON CHARACTERISTICS (Note 2)								
$V_{GS(TH)}$	Gate Threshold Voltage	N	V_{GS} = V_{DS}	I_D = 250 μA	0.6	0.92	1.5	V
		P		I_D = −250 μA	−0.45	−0.83	−1.0	
$V_{GS(TH)}$ / T_J	Gate Threshold Temperature Coefficient	N				−2.1		−mV/ °C
		P				2.2		
$R_{DS(on)}$	Drain−to−Source On Resistance	N	V_{GS} = 4.5 V I_D = 0.63 A			0.29	0.375	Ω
		P	V_{GS} = −4.5 V, I_D = −0.57 A			0.22	0.30	
		N	V_{GS} = 2.5 V, I_D = 0.40 A			0.36	0.445	
		P	V_{GS} = −2.5 V, I_D = −0.48 A			0.32	0.46	
		P	V_{GS} = −1.8 V, I_D = −0.20 A			0.51	0.90	
g_{FS}	Forward Transconductance	N	V_{DS} = 4.0 V I_D = 0.63 A			2.0		S
		P	V_{DS} = −4.0 V, I_D = −0.57 A			2.0		
CHARGES AND CAPACITANCES								
C_{ISS}	Input Capacitance	N	f = 1 MHz, V_{GS} = 0 V	V_{DS} = 20 V		33	46	pF
		P		V_{DS} = −8.0V		160	225	
C_{OSS}	Output Capacitance	N		V_{DS} = 20 V		13	22	
		P		V_{DS} = −8.0 V		38	55	
C_{RSS}	Reverse Transfer Capacitance	N		V_{DS} = 20 V		2.8	5.0	
		P		V_{DS} = −8.0 V		28	40	
$Q_{G(TOT)}$	Total Gate Charge	N	V_{GS} = 4.5 V, V_{DS} = 10 V, I_D = 0.7 A			1.3	3.0	nC
		P	V_{GS} = −4.5 V, V_{DS} = −5.0 V, I_D = −0.6 A			2.2	4.0	
$Q_{G(TH)}$	Threshold Gate Charge	N	V_{GS} = 4.5 V, V_{DS} = 10 V, I_D = 0.7 A			0.1		
		P	V_{GS} = −4.5 V, V_{DS} = −5.0 V, I_D = −0.6 A			0.1		
Q_{GS}	Gate−to−Source Charge	N	V_{GS} = 4.5 V, V_{DS} = 10 V, I_D = 0.7 A			0.2		
		P	V_{GS} = −4.5 V, V_{DS} = −5.0 V, I_D = −0.6 A			0.5		
Q_{GD}	Gate−to−Drain Charge	N	V_{GS} = 4.5 V, V_{DS} = 10 V, I_D = 0.7 A			0.4		
		P	V_{GS} = −4.5 V, V_{DS} = −5.0 V, I_D = −0.6 A			0.5		
SWITCHING CHARACTERISTICS (Note 3)								
$t_{d(ON)}$	Turn−On Delay Time	N	V_{GS} = 4.5 V, V_{DD} = 10 V, I_D = 0.5 A, R_G = 20 Ω			0.083		μs
t_r	Rise Time					0.227		
$t_{d(OFF)}$	Turn−Off Delay Time					0.786		
t_f	Fall Time					0.506		
$t_{d(ON)}$	Turn−On Delay Time	P	V_{GS} = −4.5 V, V_{DD} = −4.0 V, I_D = −0.5 A, R_G = 8.0 Ω			0.013		
t_r	Rise Time					0.023		
$t_{d(OFF)}$	Turn−Off Delay Time					0.050		
t_f	Fall Time					0.036		
DRAIN−SOURCE DIODE CHARACTERISTICS								
V_{SD}	Forward Diode Voltage	N	V_{GS} = 0 V, T_J = 25°C	I_S = 0.23 A		0.76	1.1	V
		P		I_S = −0.23 A		0.76	1.1	
		N	V_{GS} = 0 V, T_J = 125°C	I_S = 0.23 A		0.63		
		P		I_S = −0.23 A		0.63		
t_{RR}	Reverse Recovery Time	N	V_{GS} = 0 V, d_{IS}/d_t = 90 A/μs	I_S = 0.23 A		0.410		μs
		P		I_S = −0.23 A		0.078		

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

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TYPICAL N−CHANNEL PERFORMANCE CURVES (T_J = 25°C UNLESS OTHERWISE NOTED)

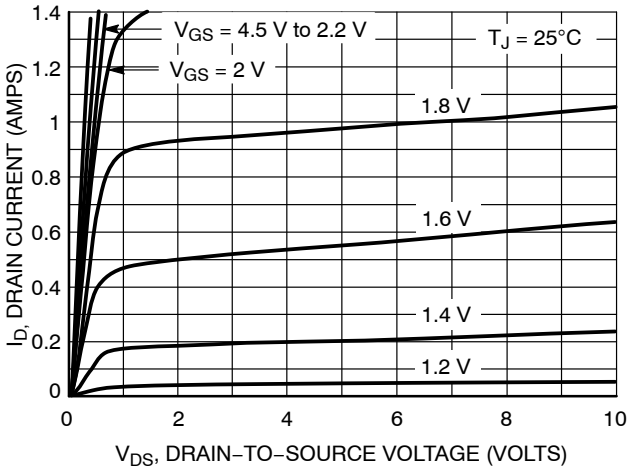


Figure 1. On−Region Characteristics

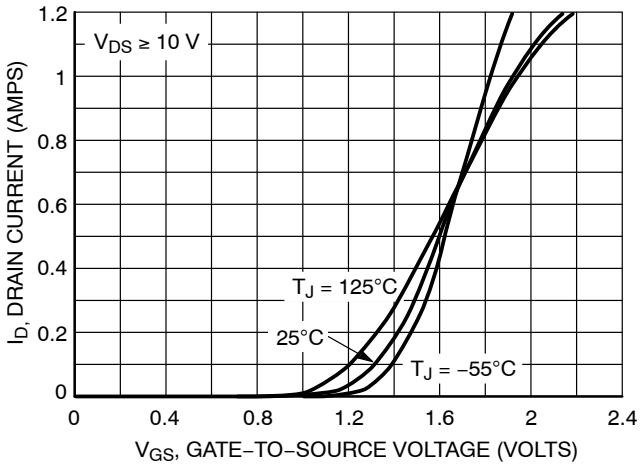


Figure 2. Transfer Characteristics

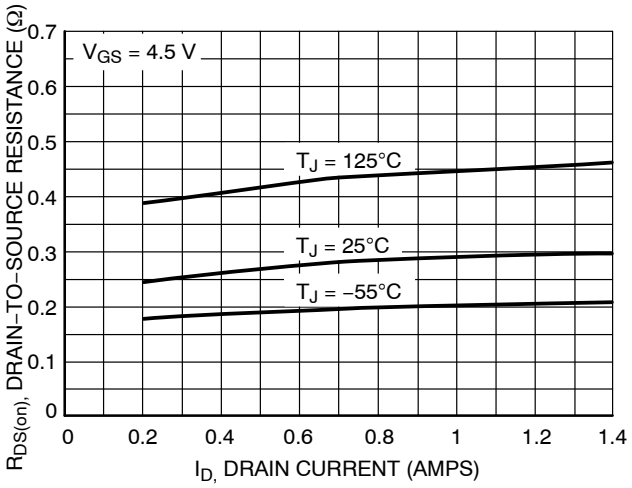


Figure 3. On−Resistance vs. Drain Current and Temperature

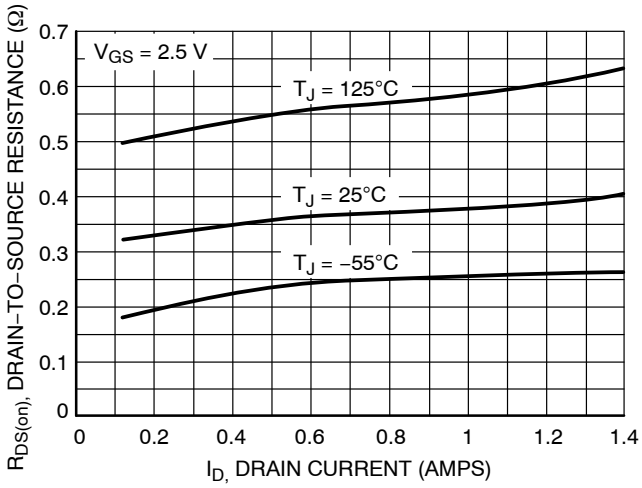


Figure 4. On−Resistance vs. Drain Current and Temperature

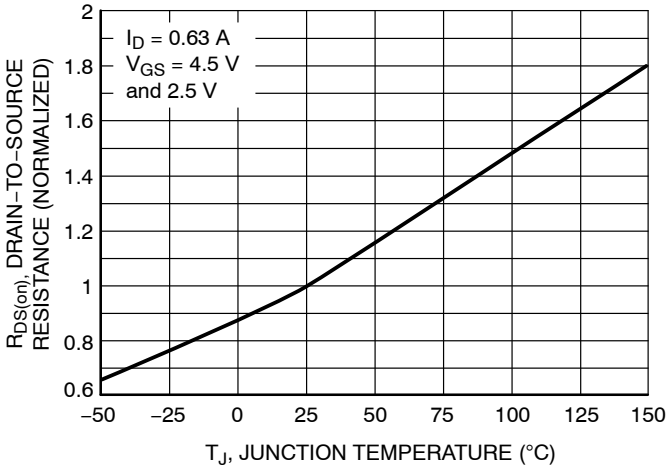


Figure 5. On−Resistance Variation with Temperature

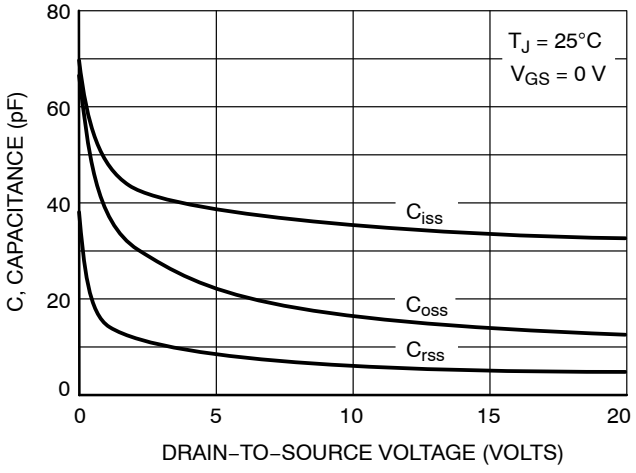


Figure 6. Capacitance Variation

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TYPICAL N−CHANNEL PERFORMANCE CURVES (T_J = 25°C UNLESS OTHERWISE NOTED) (continued)

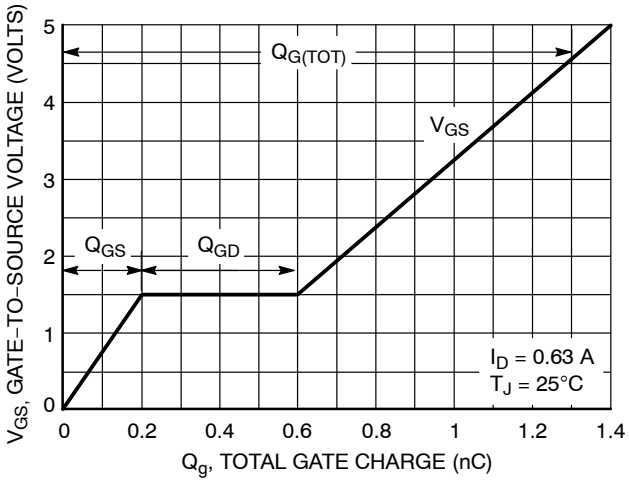


Figure 7. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

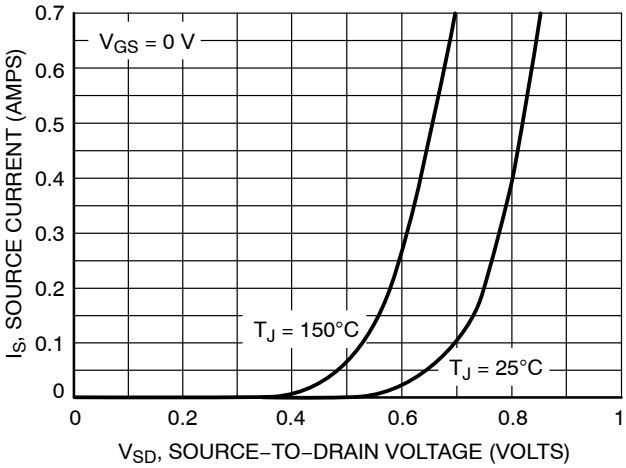


Figure 8. Diode Forward Voltage vs. Current

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TYPICAL P−CHANNEL PERFORMANCE CURVES (T_J = 25°C UNLESS OTHERWISE NOTED) (continued)

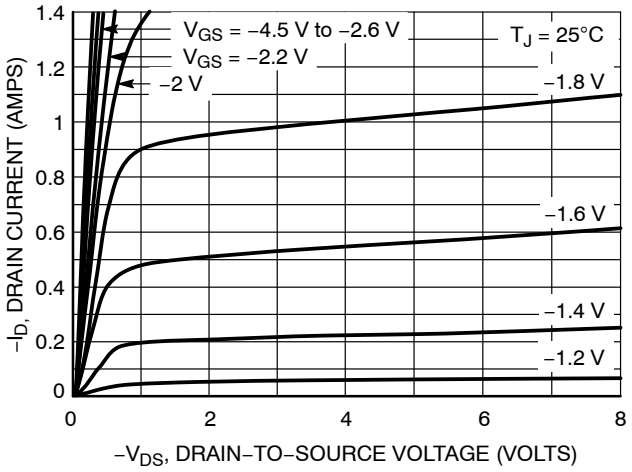


Figure 9. On−Region Characteristics

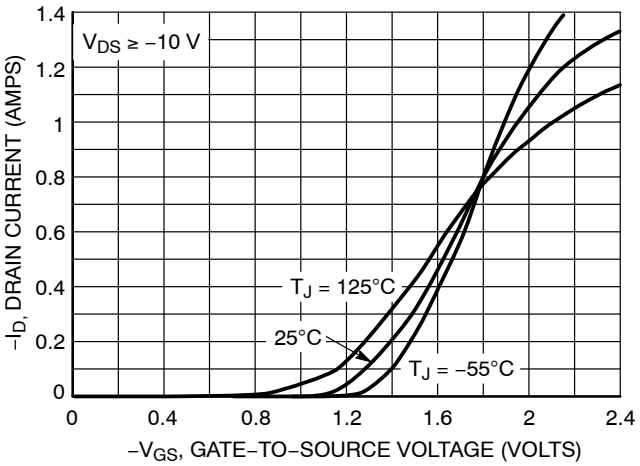


Figure 10. Transfer Characteristics

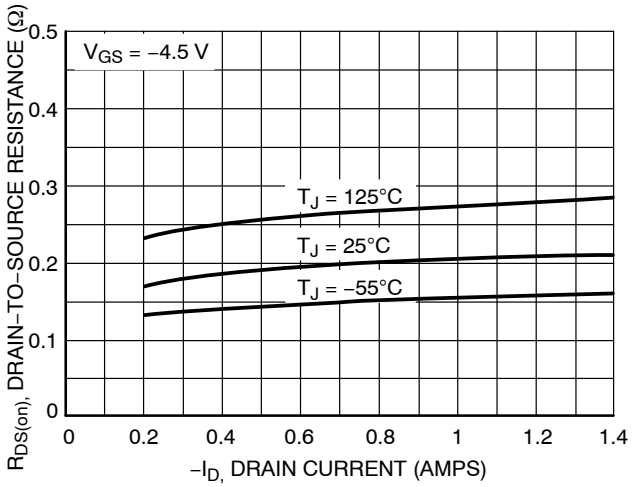


Figure 11. On−Resistance vs. Drain Current and Temperature

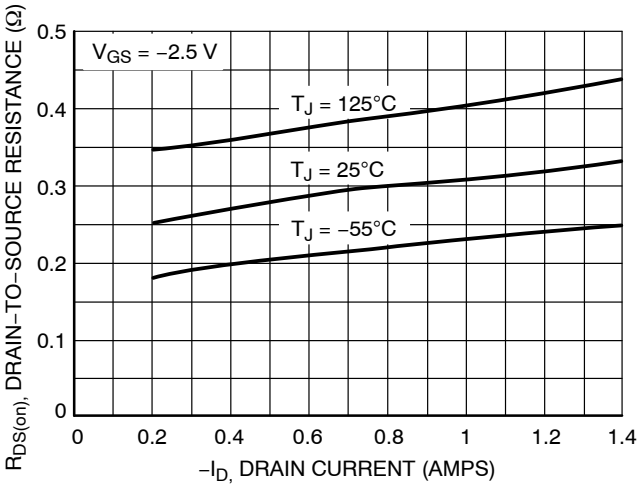


Figure 12. On−Resistance vs. Drain Current and Temperature

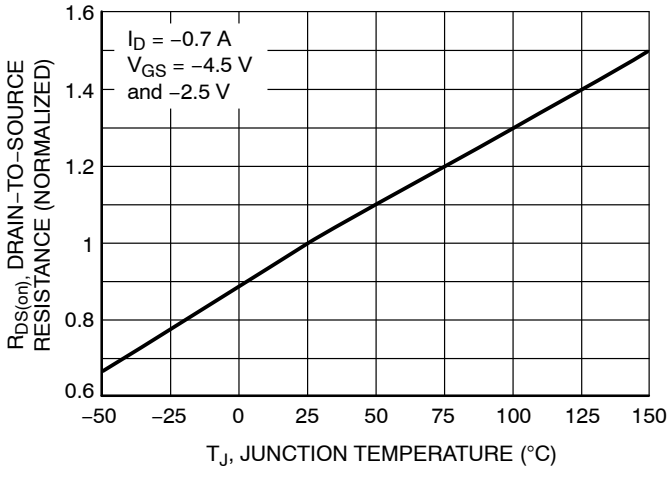


Figure 13. On−Resistance Variation with Temperature

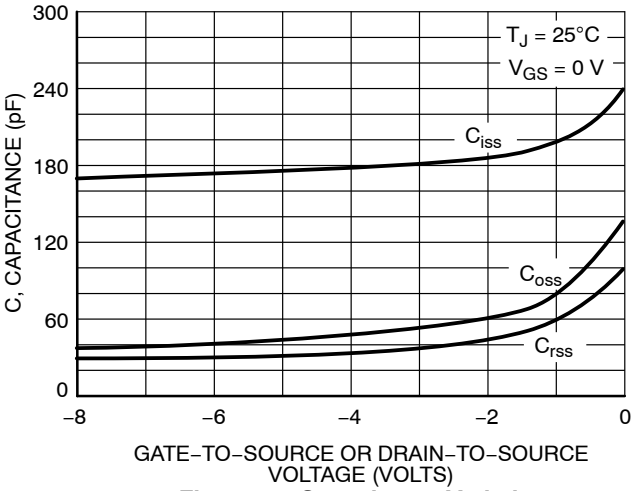


Figure 14. Capacitance Variation

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TYPICAL P−CHANNEL PERFORMANCE CURVES (T_J = 25°C UNLESS OTHERWISE NOTED) (continued)

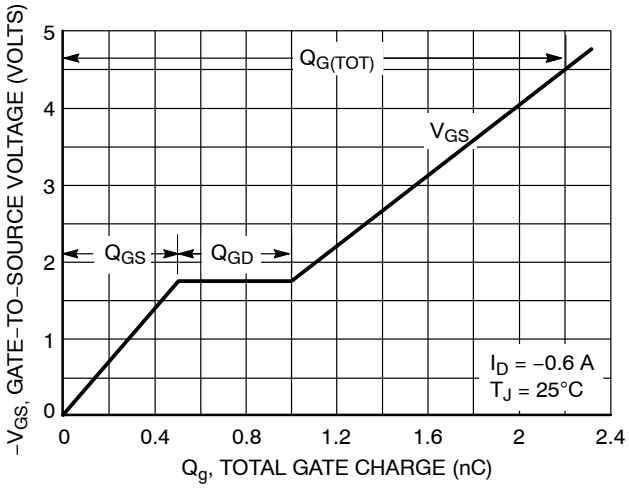


Figure 15. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

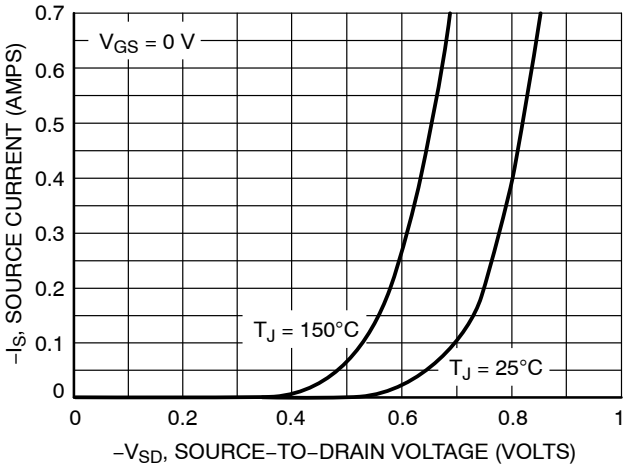


Figure 16. Diode Forward Voltage vs. Current

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ORDERING INFORMATION

Device	Package	Shipping†
NTJD4105CT1G	SOT−363 (Pb−Free)	3000 / Tape & Reel
NTJD4105CT2G	SOT−363 (Pb−Free)	3000 / Tape & Reel

DISCONTINUED (Note 4)

NTJD4105CT1	SOT−363	3000 / Tape & Reel
NTJD4105CT2	SOT−363	3000 / Tape & Reel
NTJD4105CT4	SOT−363	10,000 / Tape & Reel
NTJD4105CT4G	SOT−363 (Pb−Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

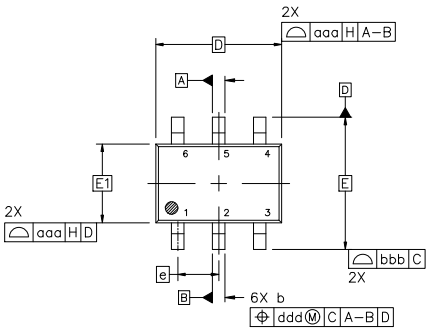
4. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

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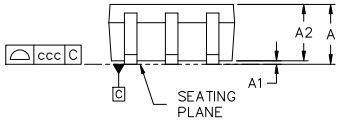


SC−88 2.00x1.25x0.90, 0.65P
CASE 419B−02
ISSUE Z

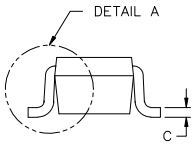
DATE 18 APR 2024



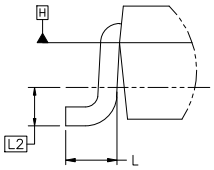
TOP VIEW



SIDE VIEW



END VIEW

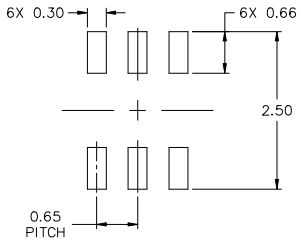


DETAIL A
SCALE 2:1

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

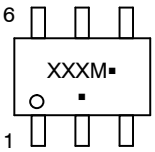
	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	−−−	−−−	1.10
A1	0.00	−−−	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42985B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SC−88 2.00x1.25x0.90, 0.65P**		**PAGE 1 OF 2**

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SC−88 2.00x1.25x0.90, 0.65P
CASE 419B−02
ISSUE Z

DATE 18 APR 2024

STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 2:
CANCELLED

STYLE 3:
CANCELLED

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. COLLECTOR
4. EMITTER
5. BASE
6. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 6:
PIN 1. ANODE 2
2. N/C
3. CATHODE 1
4. ANODE 1
5. N/C
6. CATHODE 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 8:
CANCELLED

STYLE 9:
PIN 1. EMITTER 2
2. EMITTER 1
3. COLLECTOR 1
4. BASE 1
5. BASE 2
6. COLLECTOR 2

STYLE 10:
PIN 1. SOURCE 2
2. SOURCE 1
3. GATE 1
4. DRAIN 1
5. DRAIN 2
6. GATE 2

STYLE 11:
PIN 1. CATHODE 2
2. CATHODE 2
3. ANODE 1
4. CATHODE 1
5. CATHODE 1
6. ANODE 2

STYLE 12:
PIN 1. ANODE 2
2. ANODE 2
3. CATHODE 1
4. ANODE 1
5. ANODE 1
6. CATHODE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 15:
PIN 1. ANODE 1
2. ANODE 2
3. ANODE 3
4. CATHODE 3
5. CATHODE 2
6. CATHODE 1

STYLE 16:
PIN 1. BASE 1
2. EMITTER 2
3. COLLECTOR 2
4. BASE 2
5. EMITTER 1
6. COLLECTOR 1

STYLE 17:
PIN 1. BASE 1
2. EMITTER 1
3. COLLECTOR 2
4. BASE 2
5. EMITTER 2
6. COLLECTOR 1

STYLE 18:
PIN 1. VIN1
2. VCC
3. VOUT2
4. VIN2
5. GND
6. VOUT1

STYLE 19:
PIN 1. I OUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 21:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. N/C
6. CATHODE 1

STYLE 22:
PIN 1. D1 (i)
2. GND
3. D2 (i)
4. D2 (c)
5. VBUS
6. D1 (c)

STYLE 23:
PIN 1. Vn
2. CH1
3. Vp
4. N/C
5. CH2
6. N/C

STYLE 24:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1

STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 27:
PIN 1. BASE 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. EMITTER 2
6. COLLECTOR 2

STYLE 28:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 29:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE/ANODE
6. CATHODE

STYLE 30:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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